

EAST Search History

(13 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(hoffman.in. hewlett.as.) and ("ZnSnO.sub."\$2 ("Zn.sub."\$1 near1 "SnO.sub."\$1) zinc adj (stannate orthostannate metastannate).clm. and (thin adj film adj transistor tft).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 20:04
S1	3	(("5,470,768") or ("5,879,973") or ("6,569,720")).PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2006/11/24 13:36
S2	20	(("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:48
S3	10	(("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:53
S4	1	("20030013261").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:52
S5	11	S3 S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:53
S6	9	(("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462")).PN. or ((2002/0153587) or (2002/0171085)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:56

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S7	11	(("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:57
S8	0	ep-0040076\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:58
S9	0	ep-00040076\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:59
S10	82	sasano.in.	EPO	OR	OFF	2005/10/01 17:02
S11	0	sasano.in. and drain and compound	EPO	OR	OFF	2005/10/01 17:01
S12	0	sasano.in. and drain	EPO	OR	OFF	2005/10/01 17:02
S13	4	sasano.in. and semiconductor	EPO	OR	OFF	2005/10/01 17:02
S14	1	(EP-40076-\$).did.	EPO	OR	OFF	2005/10/01 17:08
S15	4	(("5,744,864") or ("20020101557")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:08
S16	2	(("5,744,864") or ("20020101557")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 17:08
S17	2	channel near6 (zinc adj tin adj oxide ("zn.sub."\$3 near1 "sn" near1 "O.sub."\$3 ("zn.sub."\$3"sn"\$1"o.sub."\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 17:44
S18	2	channel near6 (zinc adj stannate zinc adj tin adj oxide ("zn.sub."\$3 near1 "sn" near1 "O.sub."\$3 ("zn.sub."\$3"sn"\$1"o.sub."\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 17:45
S19	2	channel near6 (stannate zinc adj stannate zinc adj tin adj oxide ("zn.sub."\$3 near1 "sn" near1 "O.sub."\$3 ("zn.sub."\$3"sn"\$1"o.sub."\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 17:45

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S20	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:58
S21	26	channel near8 (oxide near8 zinc near8 tin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 18:07
S22	26	channel near8 (oxide near8 zinc near8 tin stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 18:08
S23	89	(semiconductor adj (layer film) channel) near8 (oxide near8 zinc near8 tin stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 18:08
S24	15	(semiconductor adj (layer film) channel) near8 (oxide near8 zinc near8 tin stannate) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 18:08
S25	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2005/10/01 19:12
S26	2	thin adj film adj transistor and zto	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 19:16
S27	0	"574464".pn. and electrode near6 ITO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 20:14
S28	377	thin adj film adj transistor and (dielectric gate adj insulati\$2) near6 (sapphire alumin\$1um adj oxide titanium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:15
S29	42	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2)) near4 (sapphire alumin\$1um adj oxide titanium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:19

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S30	4	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2)) near4 (sapphire alumin\$1um adj oxide titanium adj oxide) and first adj insulati\$2 and second adj insulati\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:21
S31	5	thin adj film adj transistor.ti,ab, clm. and gate adj (oxide insulati\$2) near6 titanium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:22
S32	41	thin adj film adj transistor.ti,ab, clm. and gate adj (oxide insulati\$2) near6 (alumin\$1um adj oxide titanium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:22
S33	0	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2) near6 (alumin\$1um adj oxide) near6 (titanium adj oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:24
S34	0	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2)) near6 (lamine) near6 titanium near6 aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:24
S35	0	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 (lamine) near6 titanium near6 aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:25
S36	34	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 titanium near6 aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:30
S37	13	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 titanium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:19

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S38	0	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 titanium adj oxide and (gate adj (oxide insulati\$2)) near6 alumin\$1um adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:32
S39	36	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 alumin\$1um adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:32
S40	2	jp-60198861\$-.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:43
S41	473	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:45
S42	157	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:46
S43	157	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:46
S44	157	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin and "zn.sub.2sno. sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:47
S45	0	transparent adj gate adj electrode and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin and "zn.sub.2sno. sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48

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S46	0	transparent near2 gate adj electrode and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin and "zn.sub.2sno.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
S47	0	transparent near2 gate adj electrode and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
S48	0	transparent near2 gate and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
S49	291	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
S50	264	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:49
S51	161	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:49
S52	0	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and zto	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:49
S53	0	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:50

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S54	106	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto zinc adj oxide tin adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:50
S55	52	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto zinc adj oxide tin adj oxide) and transparent.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:22
S56	0	transparent near2 electrode and active adj matrix adj display.ti,ab, clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto zinc adj oxide tin adj oxide) and transparent.ti,ab,clm. and enhancement adj mode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:22
S57	37	(US-20020153587-\$ or US-20020171085-\$ or US-20030013261-\$ or US-20030104659-\$ or US-20030139026-\$ or US-20030180996-\$ or US-20030186489-\$ or US-20030207502-\$ or US-20030218221-\$ or US-20030218222-\$ or US-20030219530-\$ or US-20030224550-\$ or US-20050017244-\$ or US-20050199881-\$ or US-20050199880-\$ or US-20050017302-\$ or US-20040061136-\$ or US-20050040756-\$ or US-20020051099-\$).did. or (US-4559238-\$ or US-4589026-\$ or US-4887255-\$ or US-5107314-\$ or US-5470768-\$ or US-5744864-\$ or US-5879973-\$ or US-6255130-\$ or US-6255655-\$ or US-6362499-\$ or US-6391462-\$ or US-6561174-\$ or US-6569720-\$).did. or (EP-40076-\$).did. or (JP-60198861-\$).did. or (US-20050017244-\$ or US-20030218221-\$ or US-20030218222-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/01 22:23

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S58	17	enhancement adj mode.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:25
S59	0	enhancement adj mode.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm. and address adj TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:25
S60	0	enhancement adj mode.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm. and (switching address) adj TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:26
S61	4611	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/02 00:13
S62	2	S61 and ("zn.sub."\$3"sn"\$1)o.sub. 4" zinc adj stannate zto "zn.sub. "\$3 near1 "sn" near1 "o.sub."\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 00:17
S63	2	S61 and ("zn.sub."\$3"sn"\$1)o.sub. 4" zinc adj stannate zto "zn.sub. "\$3 near1 "sn" near1 "o.sub."\$3 zto)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 23:29
S64	7877	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/213) or (257/288) or (257/390) or (257/403)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/02 00:16
S65	2	S64 and ("zn.sub."\$3"sn"\$1)o.sub. 4" zinc adj stannate zto "zn.sub. "\$3 near1 "sn" near1 "o.sub."\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 00:17
S66	2	("20040023432").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 13:45

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S67	2	jp-2003086808\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 13:34
S68	2	("20030047785").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 13:34
S69	5	S66 S67 S68	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 13:45
S70	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 13:46
S71	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/03/14 13:47
S72	2	("5744864").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 15:09
S73	0	zinc adj stannate near6 (binding adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 15:14
S74	0	zinc adj stannate near6 (dissociation adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 15:09
S75	0	zinc adj stannate near12 (dissociation adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 15:10
S76	0	("Zn" near1 "Sn.sub."\$1 near1 "O. sub."\$1 zinc adj stannate) near12 (dissociation adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 15:13

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S78	0	("Zn" near1 "Sn.sub."\$1 near1 "O. sub."\$1 zinc adj stannate) near12 (ternary adj bond)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 15:14
S79	2	channel near20 ((compound) near6 (zinc near4 tin near4 oxygen) (zinc-tin-oxide zinc adj stannate zinc adj tin adj oxide tin adj zinc adj oxide tin-zinc-oxide "Zn"\$1 near1 "Sn"\$1 near1 "O. sub."\$2).ti,ab,clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 16:44
S80	2	("20050017244").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 16:41
S81	2	("5744864").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 16:42
S82	8291	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/213) or (257/288) or (257/390) or (257/403)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 16:43
S83	1	S82 and channel near20 ((compound) near6 (zinc near4 tin near4 oxygen) (zinc-tin-oxide zinc adj stannate zinc adj tin adj oxide tin adj zinc adj oxide tin-zinc-oxide "Zn"\$1 near1 "Sn"\$1 near1 "O. sub."\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 16:44
S84	0	("20050045908").PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2006/03/14 19:27
S85	2	("20050045908").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/14 19:27
S86	0	(("20040127038") or ("20040023432")).PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2006/05/25 13:14

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S87	4	(("20040127038") or ("20040023432")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/25 13:18
S88	23	channel and gate and "Zn.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 13:18
S89	0	("20040127038.pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/22 16:13
S90	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/22 20:43
S91	20755	thin adj film adj transistor.ti.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 20:43
S92	101	thin adj film adj transistor.ti. and thin adj film adj transistor near4 defined	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 20:59
S93	19	weimer.in. and transistor.ti.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 21:01
S94	1	(paul near1 weimer).in. and transistor.ti.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 15:03
S95	10	"5744864"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 13:36
S96	2	("5744864").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 13:36

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S97	9	magnetron adj sputtering with ZnO with "SnO.sub.2"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 15:03
S98	3	"20040127038"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 15:53
S99	19	zinc adj stannate near3 compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 15:53
S100	2	("6184946").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 17:52
S101	0	zinc adj orthostannate and sputtering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 17:53
S102	0	zinc adj orthostannate and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 18:31
S103	0	zinc adj orthostannate and band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 18:31
S104	4	zinc adj stannate and band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 18:31
S105	0	zinc adj stannate same band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 18:32
S106	0	zinc adj stannate same energy adj2 gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 18:42

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S10 7	11956	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 18:44
S10 8	0	S107 and zinc adj (stannate orthostannate metastannate) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 18:45
S10 9	1	S107 and ("ZnSnO.sub."\$2 ("Zn. sub."\$1 near1 "SnO.sub."\$1) zinc adj (stannate orthostannate metastannate)) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 19:18
S11 0	10	("6,100,558") or ("20030185266") or ("4,521,698") or ("20040169210") or ("6,674,495")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 19:50
S11 1	643	second adj passivation and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 19:53
S11 2	3	"496768".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/24 19:52
S11 3	185	second adj passivation.ti,ab,clm. and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 19:53
S11 4	141	second adj passivation.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 19:53
S11 5	19	second adj passivation.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm. and passivation near4 (electrical\$2 electric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/24 19:54